

What is claimed is:

1. A method of manufacturing a semiconductor device; which comprises the steps of:

forming a copper-containing film on a
5 semiconductor substrate;
removing, with a cleaning agent, a copper oxide on a surface of said copper-containing film;
applying a nitriding treatment to the surface
of said copper-containing film from which the copper
10 oxide has been removed; and
forming a copper-diffusion prevention film comprising a silicon on said copper-containing film which has been subjected to the nitriding treatment.

15 2. A method of manufacturing a semiconductor device according to Claim 1, wherein, following the step of removing copper oxide on the surface of said copper-containing film, the step of applying the nitriding treatment to the surface of said copper-containing film
20 is performed, without allowing the semiconductor substrate on which said copper-containing film from which copper oxide has been removed is formed to be exposed to an oxygen-containing atmosphere.

25 3. A method of manufacturing a semiconductor device according to Claim 1, wherein the nitriding

treatment applied to the surface of said copper-containing film is effected by a plasma treatment with a source gas comprising a nitrogen element being used.

5 4. A method of manufacturing a semiconductor device; which comprises the steps of:

 forming a copper-containing film on a semiconductor substrate;

 removing a copper oxide on a surface of said
10 copper-containing film;

 applying an anticorrosive treatment to the surface of the copper-containing film, with an anticorrosive-containing solution being used;

 carrying out a heating treatment to detach the
15 anticorrosive which is adhered onto the surface of the copper-containing film and, subsequently, applying a nitriding treatment to the surface of said copper-containing film; and

 forming a copper-diffusion prevention film
20 comprising a silicon on said copper-containing film which has been subjected to the nitriding treatment.

 5. A method of manufacturing a semiconductor device according to Claim 4, wherein the step of said
25 heating treatment is carried out in a vacuum and, thereafter, keeping the vacuum as it is, the step of

applying the nitriding treatment to the surface of said copper-containing film is performed.

6. A method of manufacturing a semiconductor device according to Claim 4, wherein the nitriding treatment applied to the surface of said copper-containing film is effected by a plasma treatment with a source gas comprising a nitrogen element being used.

10 7. A method of manufacturing a semiconductor device; which comprises the steps of:

forming a copper-containing film on a semiconductor substrate;

15 applying a nitriding treatment to the surface of said copper-containing film without allowing the semiconductor substrate to be exposed to an oxygen-containing atmosphere; and

forming a copper-diffusion prevention film comprising a silicon on said copper-containing film
20 which has been subjected to the nitriding treatment.

8. A method of manufacturing a semiconductor device according to Claim 7, wherein the nitriding treatment applied to the surface of said copper-containing film is effected by a plasma treatment with a
25 source gas comprising a nitrogen element being used.